



PATENT
Attv. Dkt. 6303/CPI/COPPER/PJS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of:

Chung, et al.

Serial No.: 09/965,370

Confirmation No.: Unknown

Filed: September 26, 2001

For: Integration of Barrier Layer
and Seed Layer

Group Art Unit: Unknown

Examiner: Unknown

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

CERTIFICATE OF MAILING
37 CFR 1.8

I hereby certify that this correspondence is being deposited on February 14, 2002 with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.

Date 2/19/02

Signature

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Supplemental Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

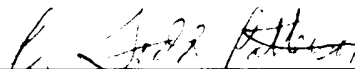
In accordance with 37 CFR § 1.97, this Supplemental Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

Form PTO-1449

180.00 CH

The Applicants do not feel that a fee is necessary at this time, if the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/APPM/6303/CPI/COPPER/PJS/BTP.

Respectfully submitted,



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|--|--|--|--------------------------|
| U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified) | | Docket No. AMAT/6303/CPI/ COPPER/PJS | Serial No. 09/965,370 |
| LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT (Use several sheets if necessary) | | Applicant Chung, et al. | |
| Examiner Unknown | | Filing Date September 26, 2001 | Group Unknown |

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| Examiner Unknown | | | | | Filing Date September 26, 2001 | | Group Unknown | |
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Date Considered

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| | C6 | Wise, et al., "Diethyldiethoxysilane as a new precursor for SiO ₂ growth on silicon", <i>Mat. Res. Soc. Symp. Proc. Vol. 224</i> (1994), pp. 27-32. |

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| | C12 | Min, et al., "Metal-Organic Atomic-Layer Deposition of Titanium-Silicon-Nitride Films" Applied | | | | | | |

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| | C15 | Elers, et al. "NbC15 as a precursor in atomic layer epitaxy" <i>Appl. Surf. Sci.</i> Vol. 82/83 (1994) pp. |

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